

# OPA6323UR

Ultra Bright

## Ultra Red LED Chip

AlGaInP /GaAs

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer AlGaInP (P/N Type)

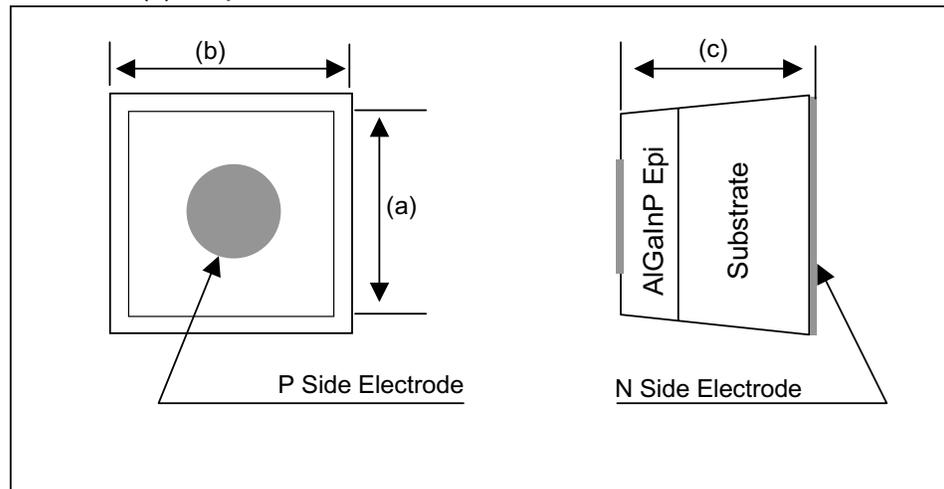
**2. Electrode** N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy

### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7		V	$I_F=1mA$
	$V_{F(2)}$		2.1	2.5	V	$I_F=20mA$
Reverse Voltage	$V_R$	6.0			V	$I_R=100\mu A$
Brightness	$I_V$	A	15	26	mcd	$I_F=20mA$
		B	25	40		
		C	35	50		
		D	48	60		
		E	58	80		
		F	68	100		
Wavelength	$\lambda_P$		632		nm	$I_F=20mA$
	$\lambda_D$		624		nm	$I_F=20mA$
	$\Delta\lambda$		20		nm	$I_F=20mA$

※ Note : Assembled into TO-18 Header without resin coating.

**4. Mechanical Data**  
 (a) Emission Area ----- 8mil × 8mil  
 (b) Bottom Area ----- 9mil × 9mil  
 (c) Chip Thickness ----- 7mil



Knowledge\*on Inc.

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